

Supporting information

Sr/Ba Substitute -Induced Higher Thermal Stability far Red-Emitting

$\text{Ba}_{1-y}\text{Sr}_y\text{LaLiWO}_6:\text{Mn}^{4+}$ Phosphor for Plant Growth Applications

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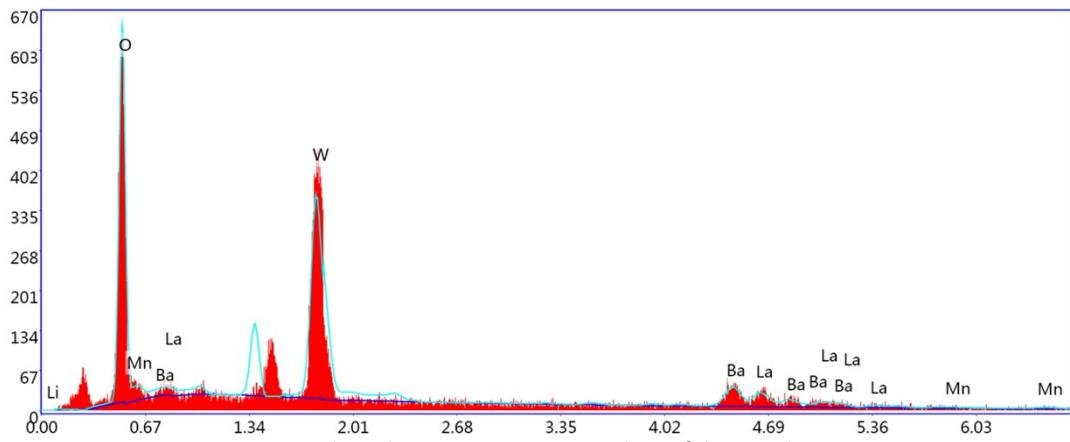


Fig. S1 Show the EDX composition analysis of the sample.

Table S1 The Rietveld refinement result of BLLW:1.2% Mn^{4+} phosphor.

compound	x = 0	x = 1.2%
Sp.gr	F m -3 m	F m -3 m
$a=b=c(\text{\AA})$	8.0975	8.0975
$\alpha=\beta=\gamma(^{\circ})$	90	90
$V(\text{\AA}^3)$	519.24	514.555
W-O bond length	1.9231	1.9234
$R_{wp}(\%)$		8.93
$R_p(\%)$		6.37
$R_B(\%)$		8.75

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Table. S2 The crystal field strength parameters of BLLW:1.2%Mn⁴⁺.

Sample	BLLW:1.2%Mn ⁴⁺
${}^4A_{2g} \rightarrow {}^4T_{1g}$	28819 cm ⁻¹
${}^4A_{2g} \rightarrow {}^4T_{2g}$	21053 cm ⁻¹
${}^2E_g \rightarrow {}^4A_{2g}$	13947 cm ⁻¹
Dq/B	2.78
B,C	757 cm ⁻¹ , 2773 cm ⁻¹
β_1	0.92

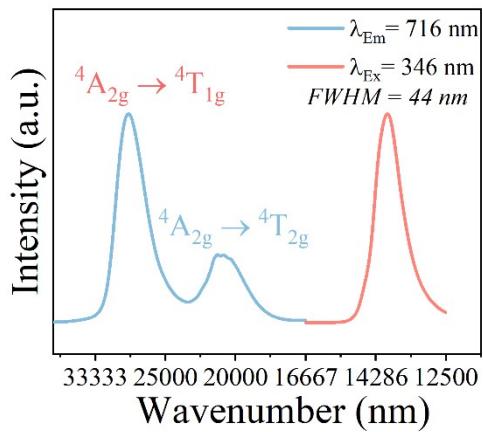


Fig. S2 The PLE and PL spectra with wavenumber of BLLW:1.2%Mn⁴⁺ phosphors

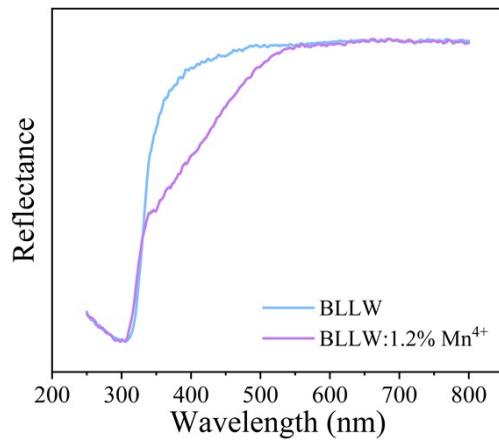


Fig. S3 Diffuse reflection spectrum of BLLW:Mn⁴⁺ and BLLW.

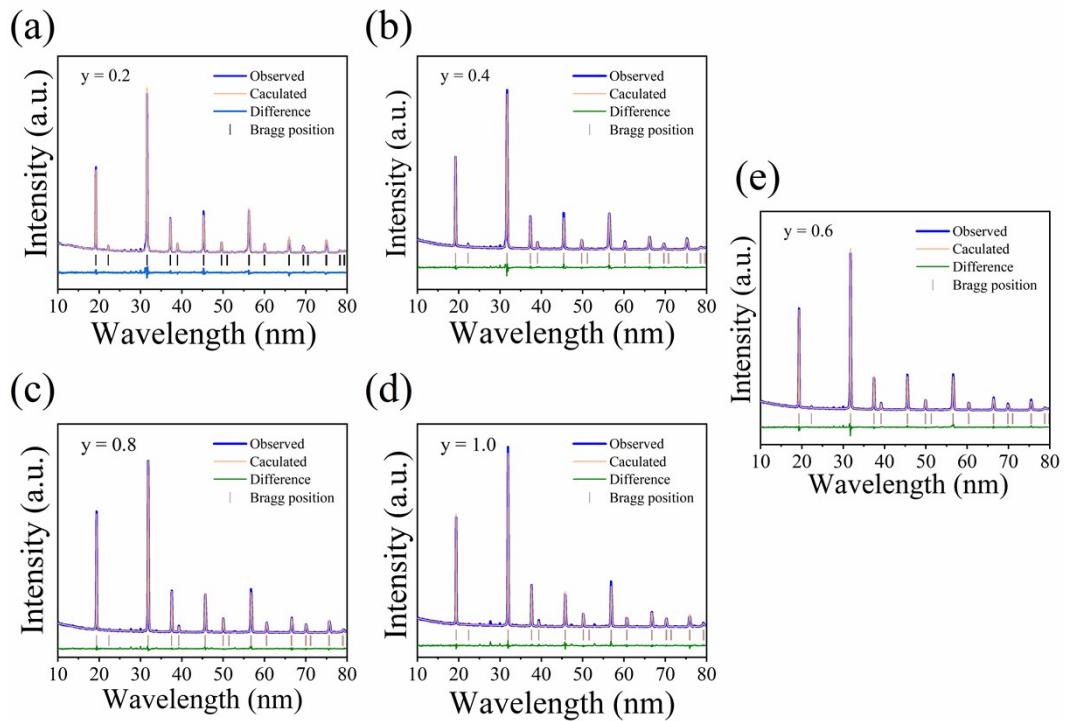


Fig. S4 Rietveld refinements of XRD profiles: (a)~(e) $\text{Ba}_{1-y}\text{Sr}_y\text{LaLiWO}_6:\text{Mn}^{4+}$

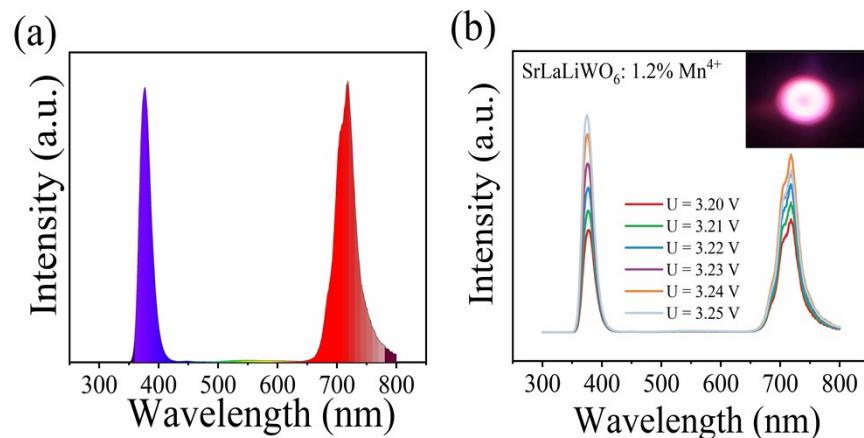


Fig. S5 (a) Electroluminescence spectra of $\text{SrLaLiWO}_6:\text{Mn}^{4+}$ coated a 365 nm NUV chip. (b) Spectra of $\text{SrLaLiWO}_6:\text{Mn}^{4+}$ phosphors coated with a 365 nm NUV chip at different voltages.